

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

Dual Common Base-Collector Bias Resistor Transistors

NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the EMC2DXV5T1G series, two complementary BRT devices are housed in the SOT-553 package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted, common for Q_1 and Q_2 , - minus sign for Q_1 (PNP) omitted)

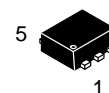
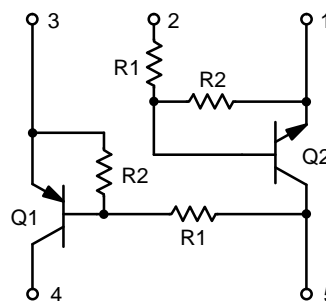
Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



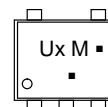
ON Semiconductor®

<http://onsemi.com>



SOT-553
CASE 463B

MARKING DIAGRAM



Ux = Specific Device Code
x = C, 3, E, or 5

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
ONE JUNCTION HEATED			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	357 (Note 1) 2.9 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 1)	$^\circ\text{C/W}$
BOTH JUNCTIONS HEATED			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	500 (Note 1) 4.0 (Note 1)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 1)	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad

DEVICE ORDERING INFORMATION, MARKING AND RESISTOR VALUES

Device	Marking	Transistor 1 – PNP		Transistor 2 – NPN		Package	Shipping†
		R1 (K)	R2 (K)	R1 (K)	R2 (K)		
EMC2DXV5T1G	UC	22	22	22	22	SOT-553 (Pb-Free)	4000 / Tape & Reel
NSVEMC2DXV5T1G*	UC	22	22	22	22		4000 / Tape & Reel
EMC3DXV5T1G	U3	10	10	10	10		4000 / Tape & Reel
EMC3DXV5T5G							8000 / Tape & Reel
EMC4DXV5T1G	UE	10	47	47	47		4000 / Tape & Reel
EMC5DXV5T1G	U5	4.7	10	47	47		4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

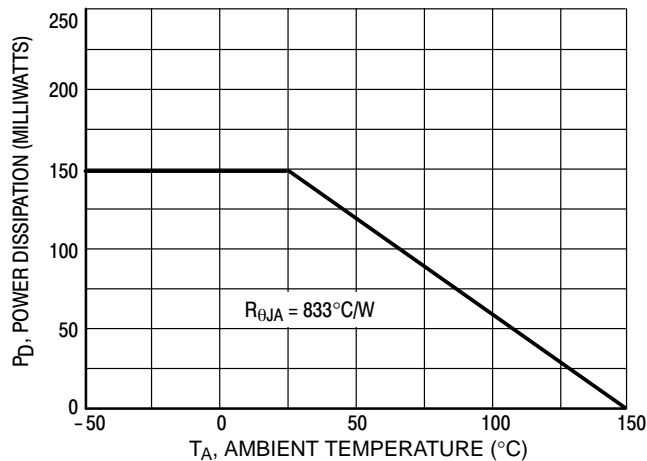


Figure 1. Derating Curve

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Q1 TRANSISTOR: PNP OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	I _{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V _{CB} = 50 V, I _B = 0)	I _{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	–	–	0.2	mAdc
	EMC2DXV5T1G	–	–	0.5	
	EMC3DXV5T1G	–	–	0.2	
	EMC4DXV5T1G	–	–	1.0	
	EMC5DXV5T1G	–	–	–	

ON CHARACTERISTICS

Collector-Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _{(BR)CBO}	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	–	–	Vdc
DC Current Gain (V _{CE} = 10 V, I _C = 5.0 mA)	h _{FE}	60	100	–	
	EMC2DXV5T1G	35	60	–	
	EMC3DXV5T1G	80	140	–	
	EMC4DXV5T1G	20	35	–	
	EMC5DXV5T1G	–	–	–	
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(SAT)}	–	–	0.25	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 kΩ)	V _{OL}	–	–	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 kΩ)	V _{OH}	4.9	–	–	Vdc
Input Resistor	R1	15.4	22	28.6	kΩ
	EMC2DXV5T1G	7.0	10	13	
	EMC3DXV5T1G	3.3	4.7	6.1	
	EMC4DXV5T1G	–	–	–	
	EMC5DXV5T1G	–	–	–	
Resistor Ratio	R1/R2	0.8	1.0	1.2	
	EMC2DXV5T1G	0.8	1.0	1.2	
	EMC3DXV5T1G	0.17	0.21	0.25	
	EMC4DXV5T1G	0.38	0.47	0.56	
	EMC5DXV5T1G	–	–	–	

Q2 TRANSISTOR: NPN OFF CHARACTERISTICS

Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	I _{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V _{CB} = 50 V, I _B = 0)	I _{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	–	–	0.2	mAdc
	EMC2DXV5T1G	–	–	0.5	
	EMC3DXV5T1G	–	–	0.1	
	EMC4DXV5T1G, EMC5DXV5T1G	–	–	–	

ON CHARACTERISTICS

Collector-Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _{(BR)CBO}	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	–	–	Vdc
DC Current Gain (V _{CE} = 10 V, I _C = 5.0 mA)	h _{FE}	60	100	–	
	EMC2DXV5T1G	35	60	–	
	EMC3DXV5T1G	80	140	–	
	EMC4DXV5T1G, EMC5DXV5T1G	–	–	–	
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(SAT)}	–	–	0.25	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 kΩ)	V _{OL}	–	–	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 kΩ)	V _{OH}	4.9	–	–	Vdc
Input Resistor	R1	15.4	22	28.6	kΩ
	EMC2DXV5T1G	7.0	10	13	
	EMC3DXV5T1G	33	47	61	
	EMC4DXV5T1G, EMC5DXV5T1G	–	–	–	
Resistor Ratio	R1/R2	0.8	1.0	1.2	
	EMC2DXV5T1G	0.8	1.0	1.2	
	EMC3DXV5T1G	0.8	1.0	1.2	
	EMC4DXV5T1G, EMC5DXV5T1G	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

TYPICAL ELECTRICAL CHARACTERISTICS – EMC2DXV5T1 PNP TRANSISTOR

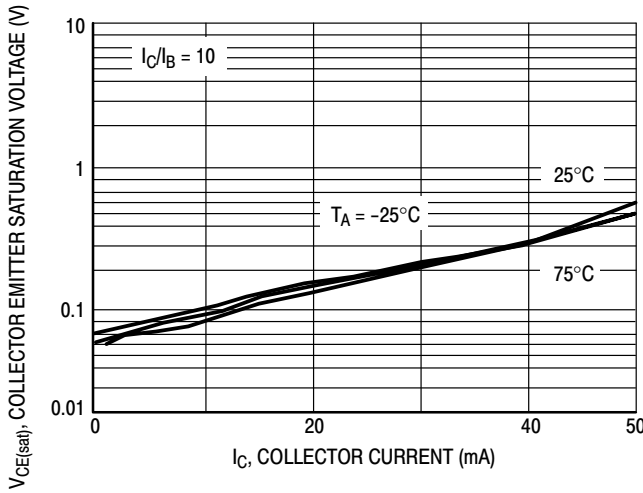


Figure 2. $V_{CE(sat)}$ versus I_C

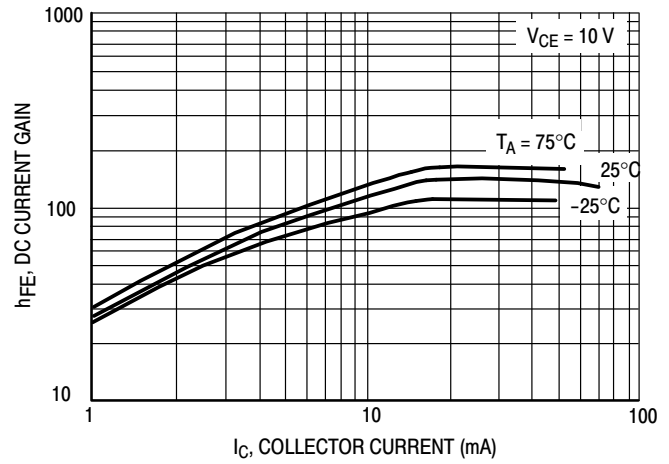


Figure 3. DC Current Gain

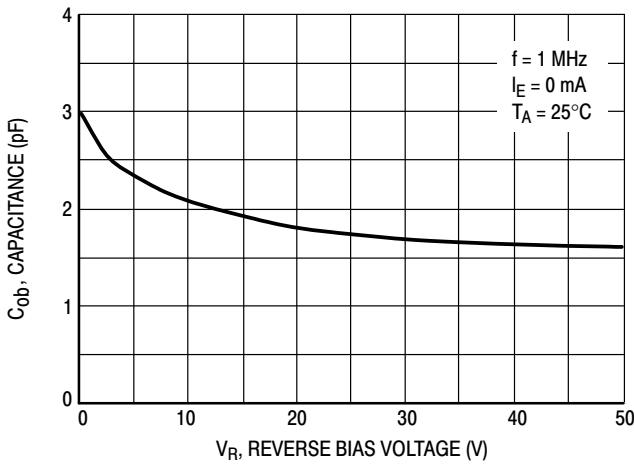


Figure 4. Output Capacitance

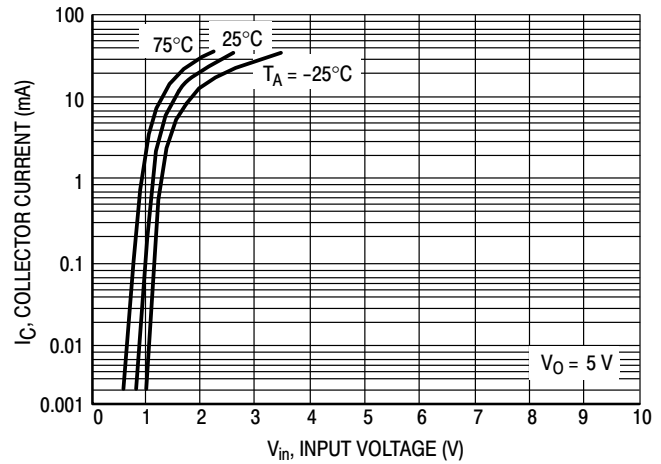


Figure 5. Output Current versus Input Voltage

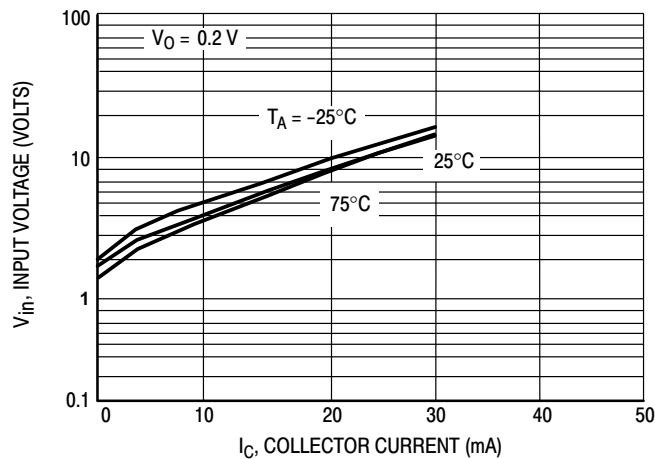


Figure 6. Input Voltage versus Output Current

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

TYPICAL ELECTRICAL CHARACTERISTICS – EMC2DXV5T1 NPN TRANSISTOR

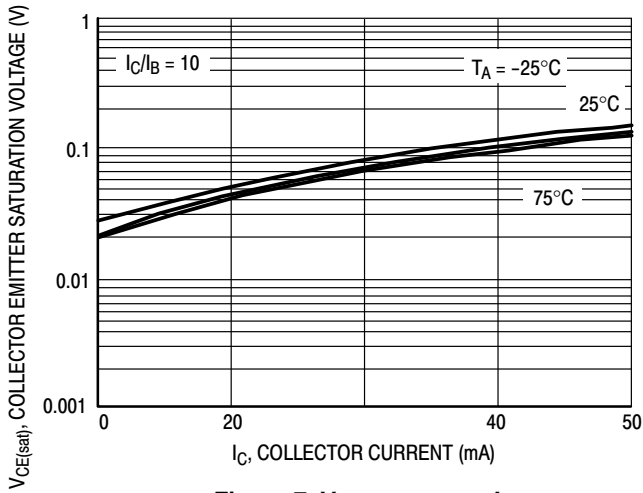


Figure 7. $V_{CE(sat)}$ versus I_C

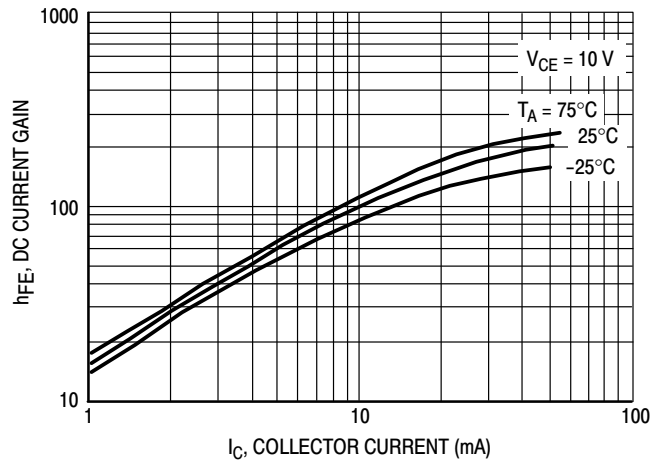


Figure 8. DC Current Gain

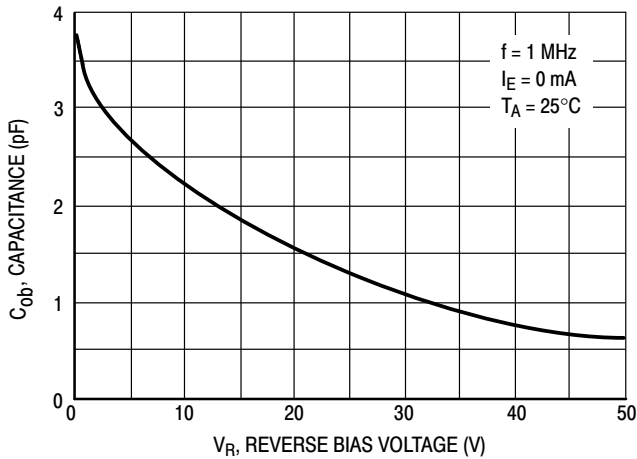


Figure 9. Output Capacitance

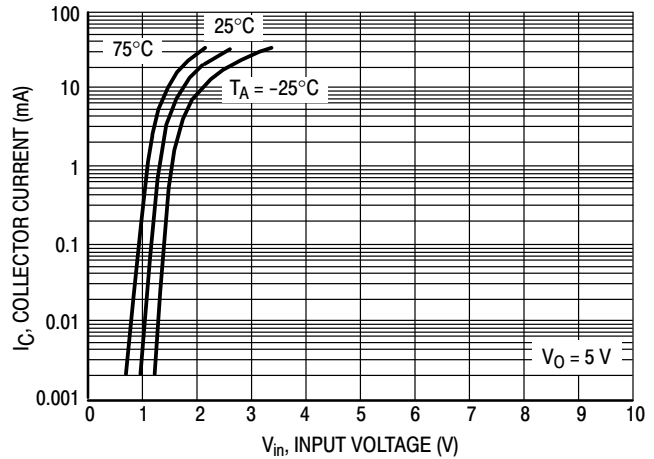


Figure 10. Output Current versus Input Voltage

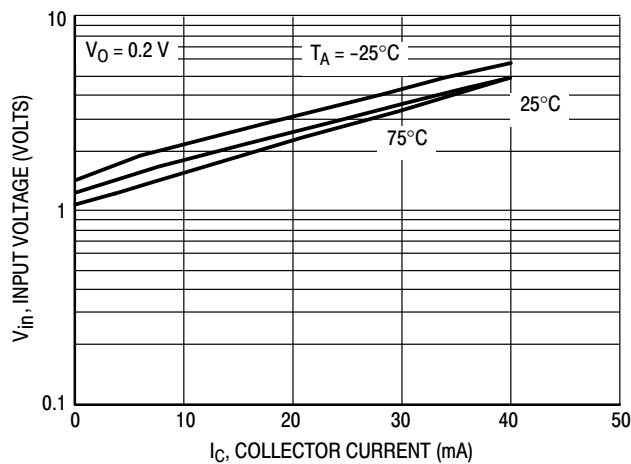


Figure 11. Input Voltage versus Output Current

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

TYPICAL ELECTRICAL CHARACTERISTICS – EMC3DXV5T1 PNP TRANSISTOR

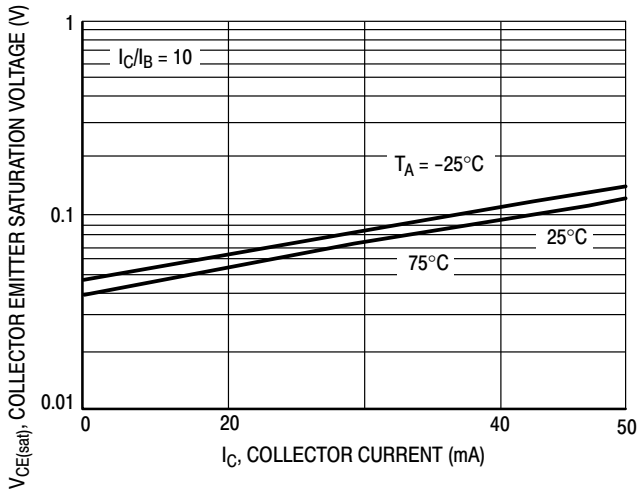


Figure 12. $V_{CE(sat)}$ versus I_C

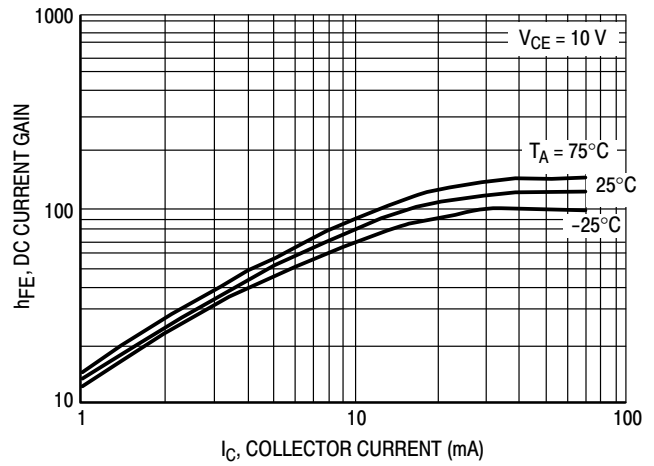


Figure 13. DC Current Gain

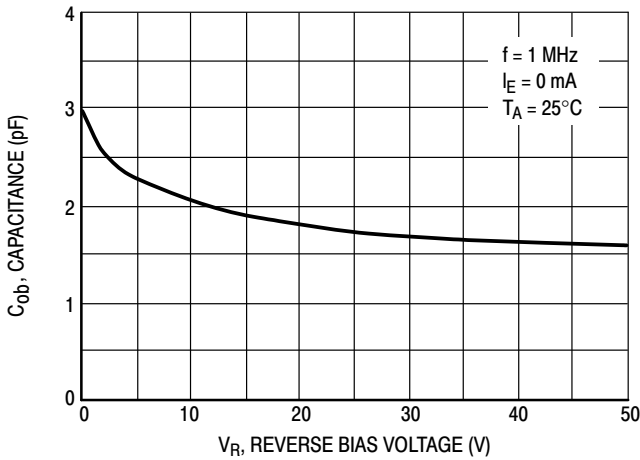


Figure 14. Output Capacitance

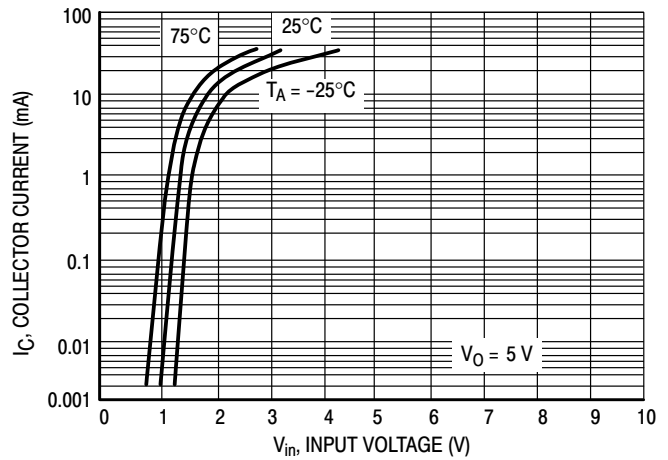


Figure 15. Output Current versus Input Voltage

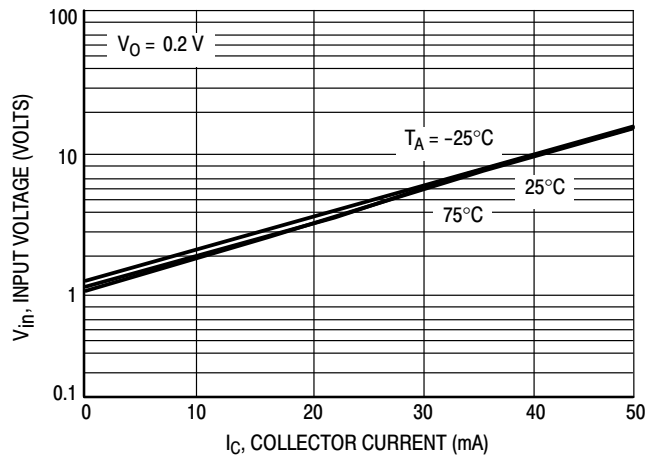


Figure 16. Input Voltage versus Output Current

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

TYPICAL ELECTRICAL CHARACTERISTICS – EMC3DXV5T1 NPN TRANSISTOR

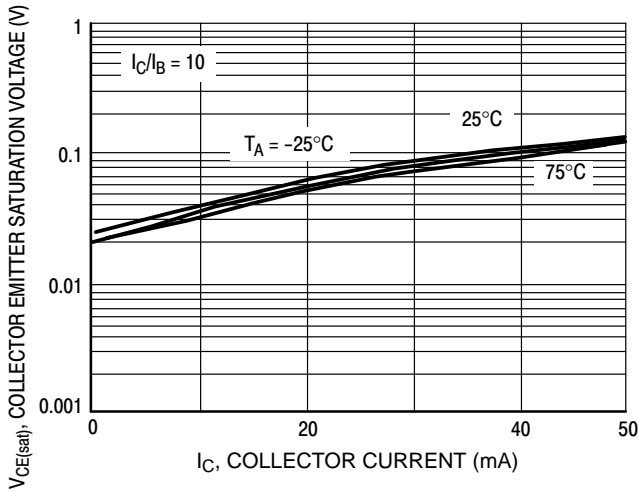


Figure 17. $V_{CE(sat)}$ versus I_C

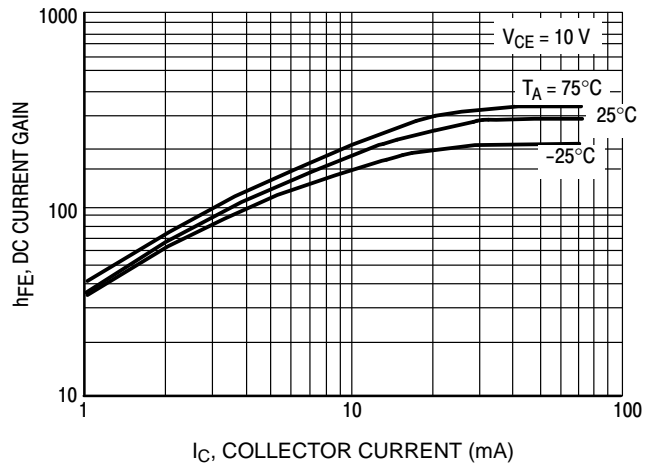


Figure 18. DC Current Gain

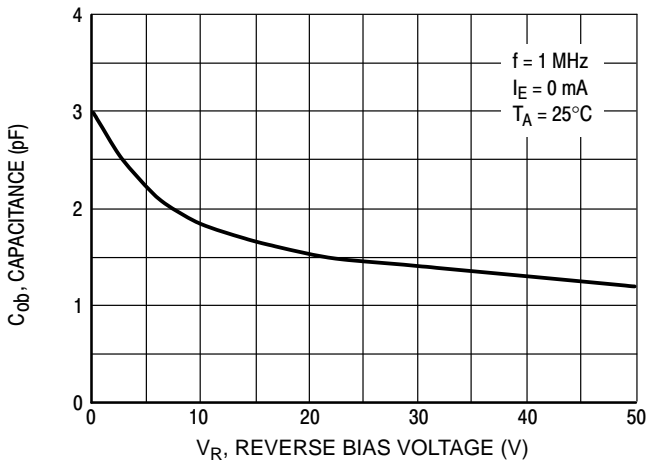


Figure 19. Output Capacitance

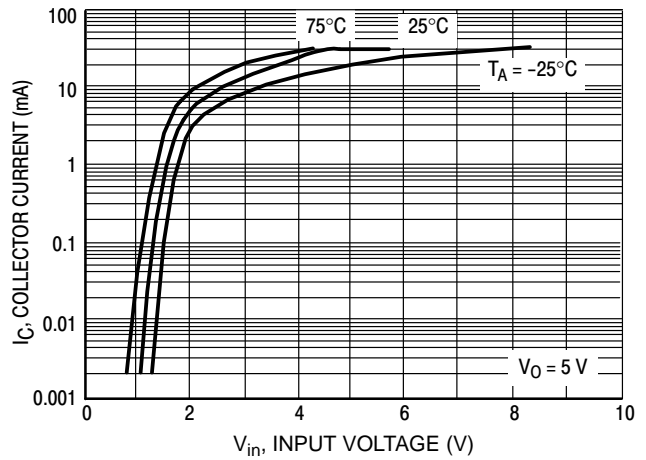


Figure 20. Output Current versus Input Voltage

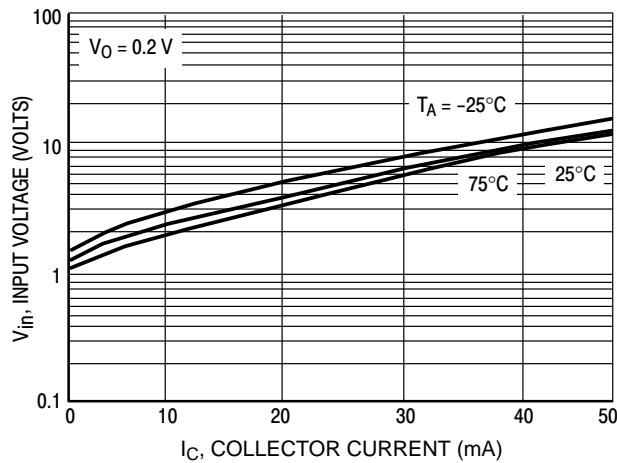


Figure 21. Input Voltage versus Output Current

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

TYPICAL ELECTRICAL CHARACTERISTICS – EMC4DXV5T1 PNP TRANSISTOR

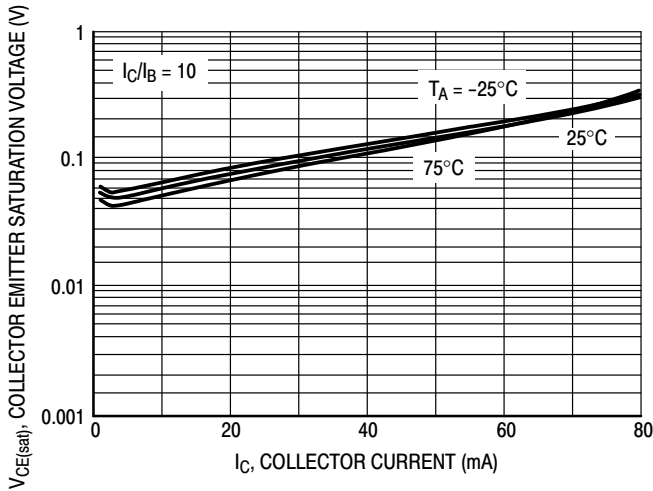


Figure 22. $V_{CE(sat)}$ versus I_C

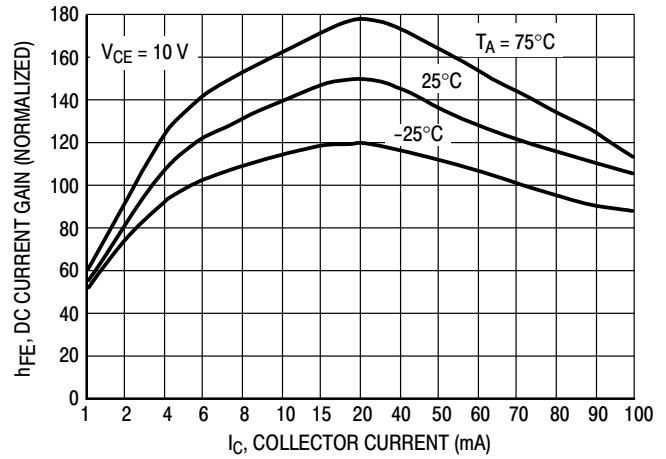


Figure 23. DC Current Gain

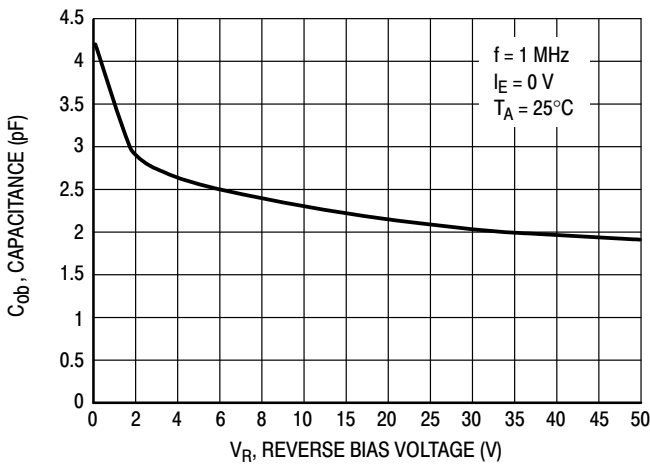


Figure 24. Output Capacitance

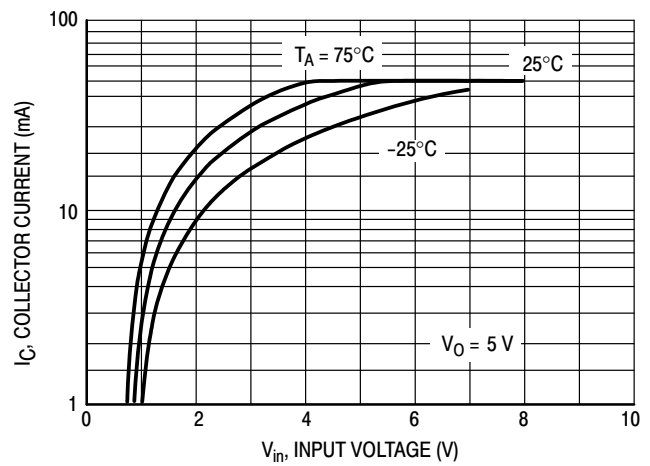


Figure 25. Output Current versus Input Voltage

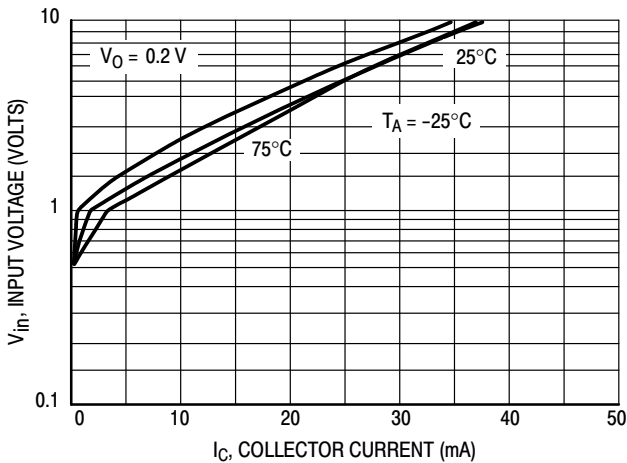


Figure 26. Input Voltage versus Output Current

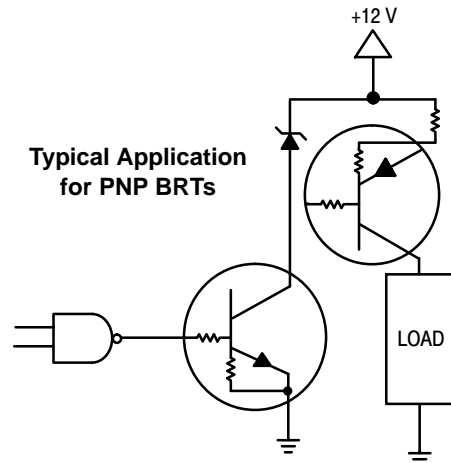


Figure 27. Inexpensive, Unregulated Current Source

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

TYPICAL ELECTRICAL CHARACTERISTICS – EMC5DXV5T1 PNP TRANSISTOR

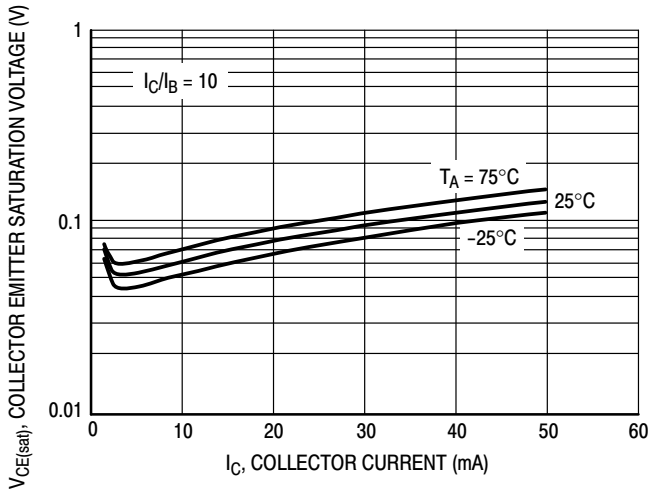


Figure 28. $V_{CE(sat)}$ versus I_C

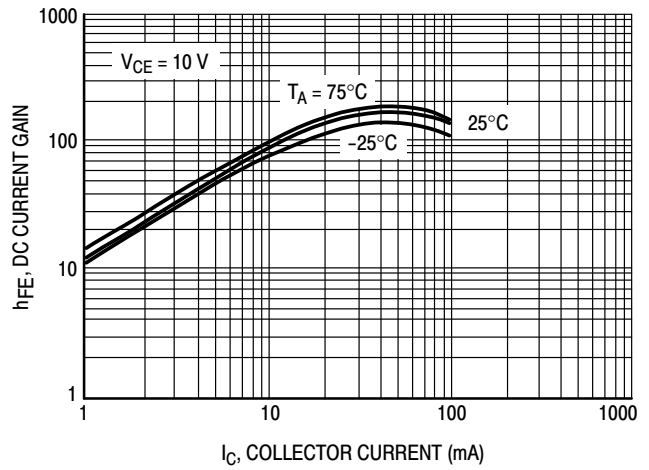


Figure 29. DC Current Gain

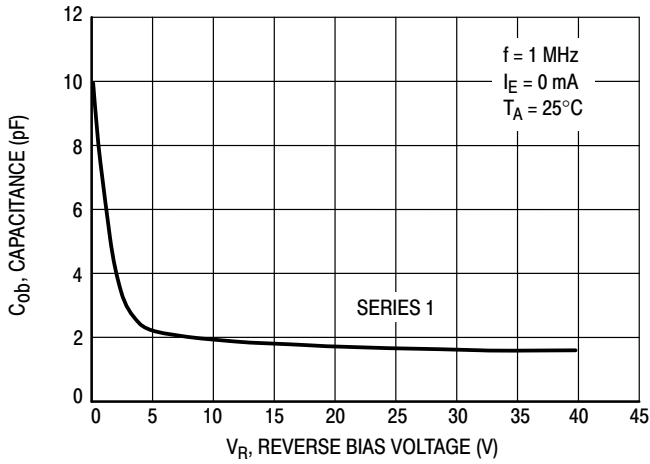


Figure 30. Output Capacitance

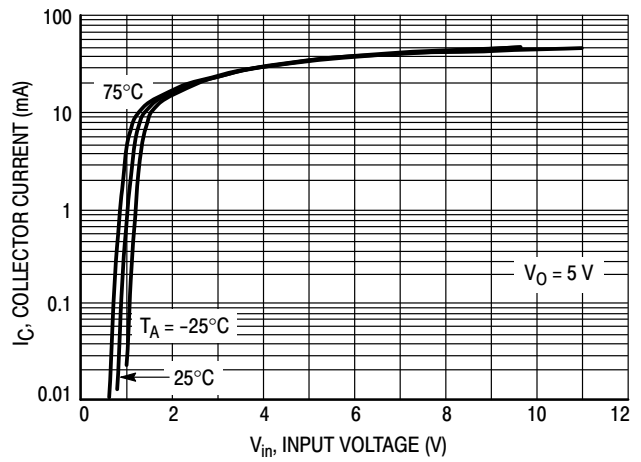


Figure 31. Output Current versus Input Voltage

EMC2DXV5T1G, EMC3DXV5T1G, EMC4DXV5T1G, EMC5DXV5T1G

TYPICAL ELECTRICAL CHARACTERISTICS – EMC4DXV5T1, EMC5DXV5T1 NPN TRANSISTOR

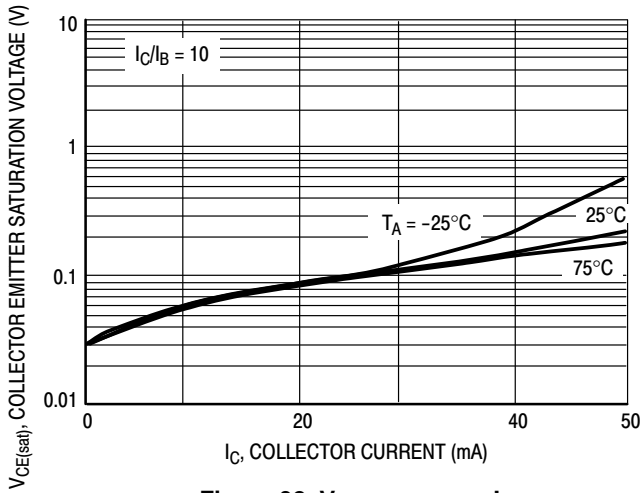


Figure 32. $V_{CE(sat)}$ versus I_C

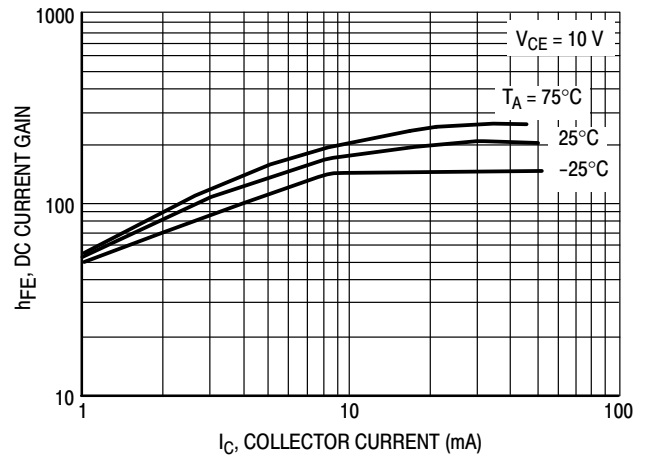


Figure 33. DC Current Gain

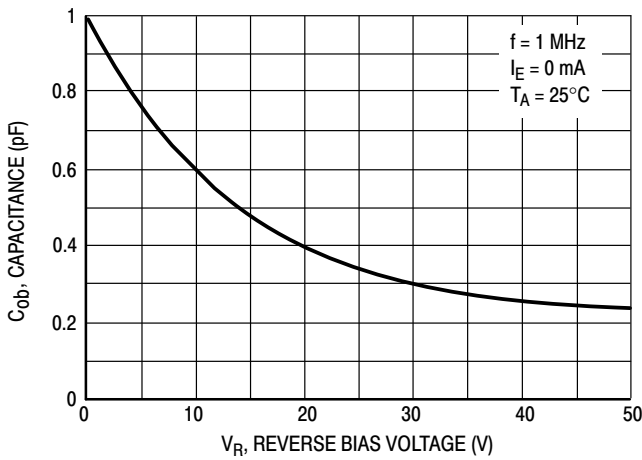


Figure 34. Output Capacitance

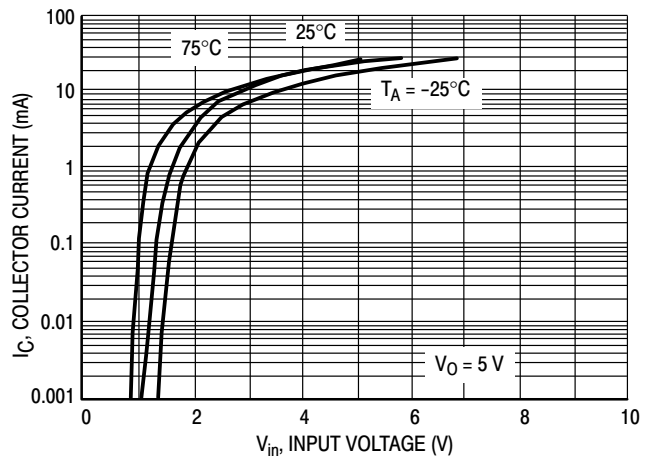


Figure 35. Output Current versus Input Voltage

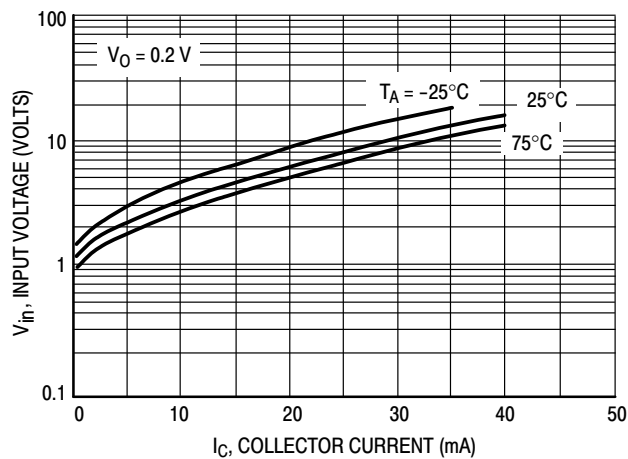


Figure 36. Input Voltage versus Output Current

MECHANICAL CASE OUTLINE

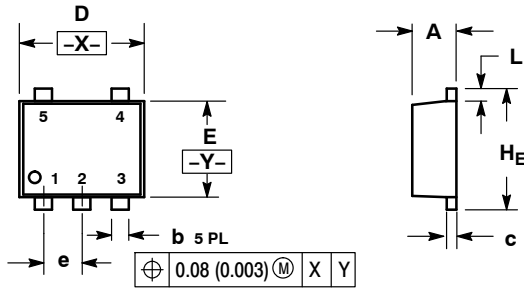
PACKAGE DIMENSIONS



SCALE 4:1

SOT-553, 5 LEAD
CASE 463B
ISSUE C

DATE 20 MAR 2013

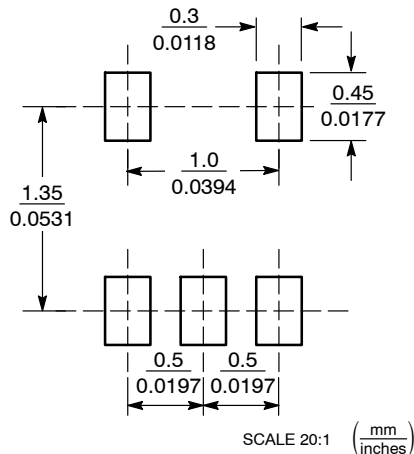


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
c	0.08	0.13	0.18	0.003	0.005	0.007
D	1.55	1.60	1.65	0.061	0.063	0.065
E	1.15	1.20	1.25	0.045	0.047	0.049
e	0.50 BSC			0.020 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H _E	1.55	1.60	1.65	0.061	0.063	0.065

RECOMMENDED SOLDERING FOOTPRINT*



GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLE 1:

1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:

1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 3:

1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:

1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:

1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 6:

1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR 1
5. COLLECTOR 2/BASE 1

STYLE 7:

1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:

1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:

1. ANODE
2. CATHODE
3. ANODE
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